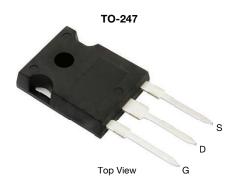


Vishay Siliconix

# N-Channel 200 V (D-S) 175 °C MOSFET



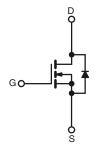
| PRODUCT SUMMARY  |                  |  |  |  |
|--|------------------|--|--|--|
| V <sub>DS</sub> (V)  | 200              |  |  |  |
| $R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10 \text{ V}$  | 0.0095           |  |  |  |
| $R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 7.5 \text{ V}$ | 0.0104           |  |  |  |
| Q <sub>g</sub> typ. (nC)                                   | 86               |  |  |  |
| I <sub>D</sub> (A)   | 100 <sup>d</sup> |  |  |  |
| Configuration  | Single           |  |  |  |

#### **FEATURES**

- ThunderFET® power MOSFET
- Low R<sub>DS</sub> Q<sub>g</sub> figure-of-merit (FOM)
- Maximum 175 °C junction temperature
- 100 % R<sub>a</sub> and UIS tested
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

## **APPLICATIONS**

- Synchronous rectification
- · Power supplies
- DC/AC inverter
- DC/DC converter
- Solar micro inverter
- · Motor drive switch



HALOGEN

**FREE** 

N-Channel MOSFET

| ORDERING INFORMATION            |               |
|---------------------------------|---------------|
| Package                         | TO-247        |
| Lead (Pb)-free and halogen-free | SUG90090E-GE3 |

| <b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>A</sub> = 25 °C, unless otherwise noted)             |                         |                                   |                  |      |
|--|-------------------------|-----------------------------------|------------------|------|
| PARAMETER  |                         | SYMBOL                            | LIMIT            | UNIT |
| Drain-source voltage   |                         | V <sub>DS</sub>                   | 200              |      |
| Gate-source voltage  |                         | V <sub>GS</sub>                   | ± 20             | V    |
| Continuous dunin comment   | T <sub>C</sub> = 25 °C  |                                   | 100 <sup>d</sup> |      |
| Continuous drain current   | T <sub>C</sub> = 125 °C | l <sub>D</sub>                    | 77.6             |      |
| Pulsed drain current (t = 100 μs)  |                         | I <sub>DM</sub>                   | 300              | A    |
| Continuous source-drain diode current  |                         | I <sub>S</sub>                    | 100 <sup>d</sup> |      |
| Single pulse avalanche current <sup>a</sup>  | . 0.1                   | I <sub>AS</sub>                   | 100              |      |
| Single pulse avalanche energy <sup>a</sup>   | L = 0.1 mH              | E <sub>AS</sub>                   | 500              | mJ   |
| Maximum power dissipation $ T_{C} = 25  ^{\circ}\text{C} $ $ T_{C} = 125  ^{\circ}\text{C} $ |                         | Б                                 | 395 <sup>b</sup> | 10/  |
|  |                         | P <sub>D</sub>                    | 132 <sup>b</sup> | W    |
| Operating junction and storage temperature range   |                         | T <sub>J</sub> , T <sub>stg</sub> | -55 to +175      | ***  |
| Soldering recommendations (peak temperature) <sup>c</sup>                                    |                         |                                   | 260              | °C   |

| THERMAL RESISTANCE RATINGS                |              |                   |         |      |
|---|--------------|-------------------|---------|------|
| PARAMETER                                 |              | SYMBOL            | MAXIMUM | UNIT |
| Maximum junction-to-ambient (PCB mount) c |              | R <sub>thJA</sub> | 40      | °C/W |
| Maximum junction-to-case (drain)          | Steady state | R <sub>thJC</sub> | 0.38    | C/W  |

- a. Duty cycle ≤ 1 %
- b. See SOA curve for voltage derating
- c. When mounted on 1" square PCB (FR4 material)
- d. Package limited



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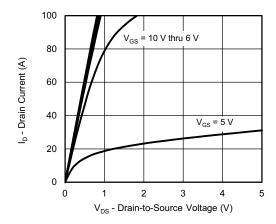
| PARAMETER                                    | SYMBOL               | TEST CONDITIONS   | MIN. | TYP.   | MAX.   | UNIT |
|--|----------------------|---|------|--------|--------|------|
| Static                                       |                      |   |      |        |        |      |
| Drain-source breakdown voltage               | $V_{DS}$             | $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$                         | 200  | -      | -      | V    |
| Gate-source threshold voltage                | V <sub>GS(th)</sub>  | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$                                  | 2    | -      | 4      | V    |
| Gate-source leakage                          | I <sub>GSS</sub>     | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$                     | -    | -      | 250    | nA   |
|  |                      | $V_{DS} = 200 \text{ V}, V_{GS} = 0 \text{ V}$                        | -    | -      | 1      |      |
| Zero gate voltage drain current              | $I_{DSS}$            | $V_{DS}$ = 200 V, $V_{GS}$ = 0 V, $T_J$ = 125 °C                      | -    | -      | 150    | μA   |
|  |                      | $V_{DS}$ = 200 V, $V_{GS}$ = 0 V, $T_J$ = 175 °C                      | -    | -      | 5      | mA   |
| On-state drain current <sup>a</sup>          | I <sub>D(on)</sub>   | $V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$                      | 30   | -      | -      | Α    |
| Drain-source on-state resistance a           | ٥                    | $V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$                           | -    | 0.0079 | 0.0095 | Ω    |
| Dialii-Source oii-state resistance "         | R <sub>DS(on)</sub>  | $V_{GS} = 7.5 \text{ V}, I_D = 15 \text{ A}$                          | -    | 0.0083 | 0.0104 | ] 52 |
| Forward transconductance <sup>a</sup>        | 9 <sub>fs</sub>      | $V_{DS} = 15 \text{ V}, I_D = 20 \text{ A}$                           | -    | 54     | -      | S    |
| Dynamic <sup>b</sup>                         |                      |   |      |        |        |      |
| Input capacitance                            | C <sub>iss</sub>     |   | -    | 5220   | -      | pF   |
| Output capacitance                           | C <sub>oss</sub>     | $V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$     | -    | 495    | -      |      |
| Reverse transfer capacitance                 | C <sub>rss</sub>     |   | -    | 51     | -      |      |
| Total gate charge                            | $Q_g$                |   | -    | 86     | 129    | nC   |
| Gate-source charge                           | $Q_{gs}$             | $V_{DS} = 100 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$ | -    | 23     | -      |      |
| Gate-drain charge                            | $Q_{gd}$             |   | -    | 22.7   | -      |      |
| Gate resistance                              | $R_{g}$              | f = 1 MHz   | 0.6  | 3.2    | 14.4   | Ω    |
| Turn-on delay time                           | t <sub>d(on)</sub>   |   | -    | 18     | 27     |      |
| Rise time                                    | t <sub>r</sub>       | $V_{DD}$ = 100 V, $R_L$ = 6.7 $\Omega$ , $I_D \cong$ 15 A,            | -    | 44     | 66     | no   |
| Turn-off delay time                          | t <sub>d(off)</sub>  | $V_{GEN}$ = 10 $V$ , $R_g$ = 1 $\Omega$                               | -    | 60     | 90     | ns   |
| Fall time                                    | t <sub>f</sub>       |   | -    | 40     | 60     |      |
| <b>Drain-Source Body Diode Characteristi</b> | cs                   |   |      |        |        |      |
| Pulse diode forward current (t = 100 μs)     | I <sub>SM</sub>      |   | -    | -      | 100    | Α    |
| Body diode voltage                           | V <sub>SD</sub>      | I <sub>F</sub> = 15 A, V <sub>GS</sub> = 0 V                          | -    | 0.85   | 1.5    | V    |
| Body diode reverse recovery time             | t <sub>rr</sub>      |   | -    | 146    | 220    | ns   |
| Body diode reverse recovery charge           | Q <sub>rr</sub>      | L = 15 A di/d+ = 100 A/vo   | -    | 0.91   | 1.37   | μC   |
| Reverse recovery fall time                   | t <sub>a</sub>       | I <sub>F</sub> = 15 A, di/dt = 100 A/μs                               | -    | 115    | -      |      |
| Reverse recovery rise time                   | t <sub>b</sub>       |   | -    | 31     | -      | ns   |
| Body diode peak reverse recovery charge      | I <sub>RM(REC)</sub> |   | -    | 12     | 18     | Α    |

## Notes

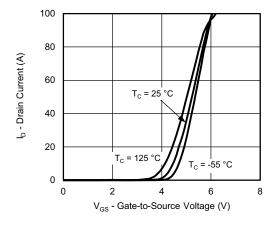
- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

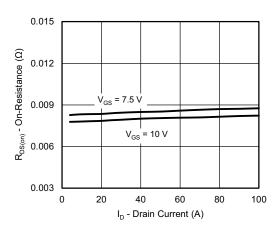




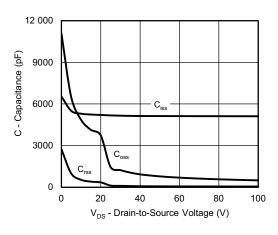
### **Output Characteristics**



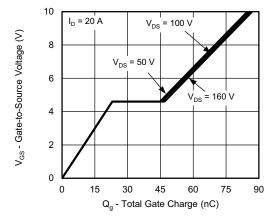
**Transfer Characteristics** 



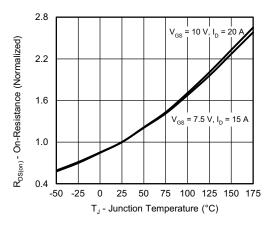
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

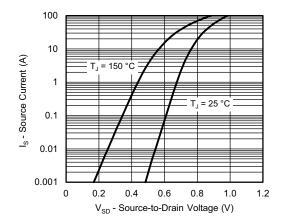


**Gate Charge** 

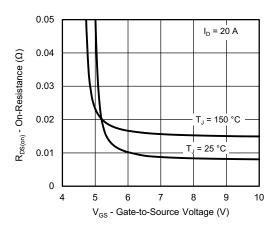


On-Resistance vs. Junction Temperature

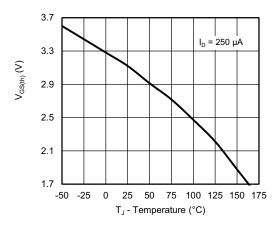




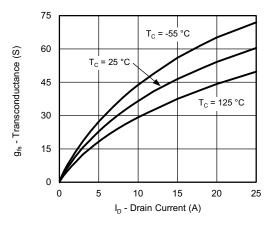
Source-Drain Diode Forward Voltage



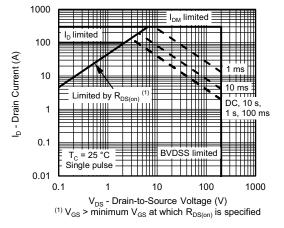
On-Resistance vs. Gate-to-Source Voltage



**Threshold Voltage** 

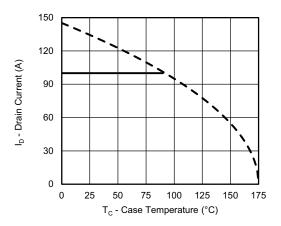


Transconductance

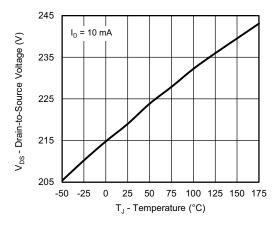


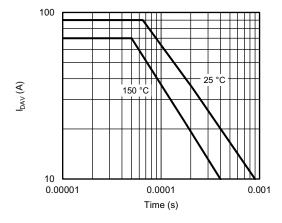
Safe Operating Area, Junction-to-Ambient





## Current Derating a





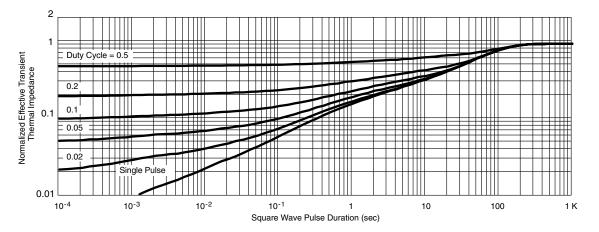
Drain Source Breakdown vs. Junction Temperature

I<sub>DAV</sub> vs. Time

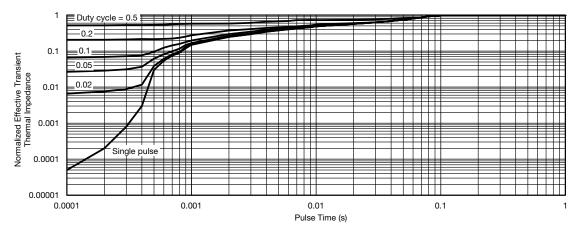
## Note

a. The power dissipation P<sub>D</sub> is based on T<sub>J</sub> max. = 25 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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# **TO-247AC (High Voltage)**

#### **VERSION 1: FACILITY CODE = 9**







Section C--C,D-D,E-E

|      | MILLIMETERS |       |       |       |
|------|-------------|-------|-------|-------|
| DIM. | MIN.        | NOM.  | MAX.  | NOTES |
| Α    | 4.83        | 5.02  | 5.21  |       |
| A1   | 2.29        | 2.41  | 2.55  |       |
| A2   | 1.17        | 1.27  | 1.37  |       |
| b    | 1.12        | 1.20  | 1.33  |       |
| b1   | 1.12        | 1.20  | 1.28  |       |
| b2   | 1.91        | 2.00  | 2.39  | 6     |
| b3   | 1.91        | 2.00  | 2.34  |       |
| b4   | 2.87        | 3.00  | 3.22  | 6, 8  |
| b5   | 2.87        | 3.00  | 3.18  |       |
| С    | 0.40        | 0.50  | 0.60  | 6     |
| c1   | 0.40        | 0.50  | 0.56  |       |
| D    | 20.40       | 20.55 | 20.70 | 4     |

|      |           | MILLIMETERS | S     |       |
|------|-----------|-------------|-------|-------|
| DIM. | MIN.      | NOM.        | MAX.  | NOTES |
| D1   | 16.46     | 16.76       | 17.06 | 5     |
| D2   | 0.56      | 0.66        | 0.76  |       |
| E    | 15.50     | 15.70       | 15.87 | 4     |
| E1   | 13.46     | 14.02       | 14.16 | 5     |
| E2   | 4.52      | 4.91        | 5.49  | 3     |
| е    |           | 5.46 BSC    |       |       |
| L    | 14.90     | 15.15       | 15.40 |       |
| L1   | 3.96      | 4.06        | 4.16  | 6     |
| ØΡ   | 3.56      | 3.61        | 3.65  | 7     |
| Ø P1 | 7.19 ref. |             |       |       |
| Q    | 5.31      | 5.50        | 5.69  |       |
| S    |           | 5.51 BSC    |       |       |

- (1) Package reference: JEDEC® TO247, variation AC
- (2) All dimensions are in mm
- (3) Slot required, notch may be rounded
- (4) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- (5) Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- $^{(7)}$  Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition



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### **VERSION 2: FACILITY CODE = Y**



|      | MILLIM |       |       |
|------|--------|-------|-------|
| DIM. | MIN.   | MAX.  | NOTES |
| Α    | 4.58   | 5.31  |       |
| A1   | 2.21   | 2.59  |       |
| A2   | 1.17   | 2.49  |       |
| b    | 0.99   | 1.40  |       |
| b1   | 0.99   | 1.35  |       |
| b2   | 1.53   | 2.39  |       |
| b3   | 1.65   | 2.37  |       |
| b4   | 2.42   | 3.43  |       |
| b5   | 2.59   | 3.38  |       |
| С    | 0.38   | 0.86  |       |
| c1   | 0.38   | 0.76  |       |
| D    | 19.71  | 20.82 |       |
| D1   | 13.08  | -     |       |

|      | MILLIN   |       |       |
|------|----------|-------|-------|
| DIM. | MIN.     | MAX.  | NOTES |
| D2   | 0.51     | 1.30  |       |
| Е    | 15.29    | 15.87 |       |
| E1   | 13.72    | -     |       |
| е    | 5.46     | BSC   |       |
| Øk   | 0.2      | 254   |       |
| L    | 14.20    | 16.25 |       |
| L1   | 3.71     | 4.29  |       |
| ØР   | 3.51     | 3.66  |       |
| Ø P1 | -        | 7.39  |       |
| Q    | 5.31     | 5.69  |       |
| R    | 4.52     | 5.49  |       |
| S    | 5.51 BSC |       |       |
|      |          |       |       |

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c



## **VERSION 3: FACILITY CODE = N**



|      | MILLIMETERS |       |  |
|------|-------------|-------|--|
| DIM. | MIN.        | MAX.  |  |
| Α    | 4.65        | 5.31  |  |
| A1   | 2.21        | 2.59  |  |
| A2   | 1.17        | 1.37  |  |
| b    | 0.99        | 1.40  |  |
| b1   | 0.99        | 1.35  |  |
| b2   | 1.65        | 2.39  |  |
| b3   | 1.65        | 2.34  |  |
| b4   | 2.59        | 3.43  |  |
| b5   | 2.59        | 3.38  |  |
| С    | 0.38        | 0.89  |  |
| c1   | 0.38        | 0.84  |  |
| D    | 19.71       | 20.70 |  |
| D1   | 13.08       | -     |  |

|      | MILLIM | IETERS |
|------|--------|--------|
| DIM. | MIN.   | MAX.   |
| D2   | 0.51   | 1.35   |
| E    | 15.29  | 15.87  |
| E1   | 13.46  | -      |
| е    | 5.46   | BSC    |
| k    | 0.254  |        |
| L    | 14.20  | 16.10  |
| L1   | 3.71   | 4.29   |
| N    | 7.62   | BSC    |
| Р    | 3.56   | 3.66   |
| P1   | -      | 7.39   |
| Q    | 5.31   | 5.69   |
| R    | 4.52   | 5.49   |
| S    | 5.51   | BSC    |

ECN: E22-0452-Rev. G, 31-Oct-2022

DWG: 5971

- <sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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